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STMicroelectronics BUY69A

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HIGH VOLTAGE NPN SILICON TRANSISTOR

- STM PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- HIGH POWER TO-3 PACKAGE

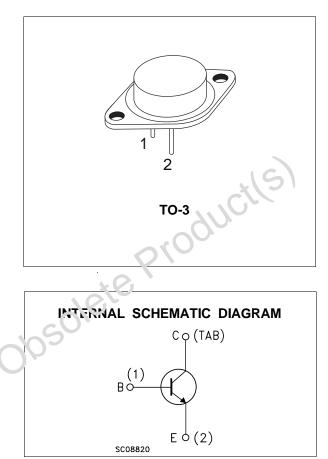
APPLICATIONS:

- HORIZONTAL DEFLECTION FOR COLOUR TV
- SWITCHING REGULATORS

DESCRIPTION

The BUY69A is a silicon Multi-Epitaxial mesa NPN transistor in Jedec TO-3 metal case. It is intended for horizontal deflection output stage of CTV receivers and high voltage, fast switching and industrial applications.

Productls



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit V	
/CES	Collector-Emitter Voltage (V _{BE} = 0)	1000		
V _{CEO}	Collector-Emitter Voltage $(I_B = 0)$	400	V	
V _{EBO}	Emitter-Base Voltage ($I_C = 0$)	8	V	
Ιc	Collector Current	10	А	
I _{CM}	Collector Peak Current (tp ≤ 10 ms)	15	А	
IB	Base Current	3	А	
P _{tot}	Total Dissipation at $T_c \le 25$ °C	100	W	
T _{stg}	Storage Temperature	-65 to 200	°C	
Tj	Max. Operating Junction Temperature	200	°C	



THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.75	°C/W
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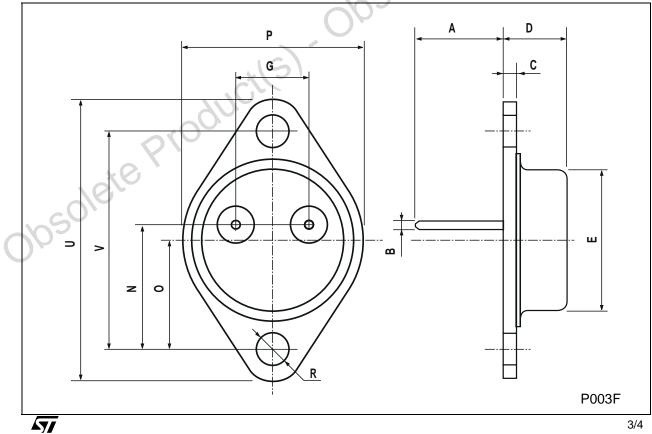
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

I _{CES} I _{EBO}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1000 V					
I _{EBO}						1	mA
	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = 8 V				1	mA
$V_{CEO(sus)}$	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA		400			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 8 A	$I_{\rm B} = 2.5 \ {\rm A}$			3.3	V
$V_{BE(sat)^*}$	Base-Emitter Saturation Voltage	I _C = 8 A	I _B = 2.5 A			2.2	V
h _{FE} *	DC Current Gain	I _C = 2.5 A	V _{CE} = 10 V	15		2	51
f⊤	Transition Frequency	I _C = 0.5 A	V _{CE} = 10 V		10	CV	МН
l _{s/b} **	Second Breakdown Collector Current	V _{CE} = 25 V		4	9)	A
t _{on}	Turn on Time	$I_{C} = 5 A$ $I_{B1} = 1 A$	V _{CE} = 250 V	2	0.2		με
t _s t _s	Storage Time Fall Time	$I_{C} = 5 A$ $I_{B1} = -I_{B2} = 1 A$	V _{CE} = 250 V			1.7 0.3	μs μs
t _f	Fall Time	$I_{C} = 8 A$ $I_{B1} = -I_{B2} = 2.5 A$	V _{CE} = 40 V			1	με
· • • • • • • • • • • • • • • • • • • •	non repetitive pulse.	otle	~				
	teprou						
	6,						



DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	11.00		13.10	0.433		0.516	
В	0.97		1.15	0.038		0.045	
С	1.50		1.65	0.059		0.065	
D	8.32		8.92	0.327		0.351	
E	19.00		20.00	0.748		0.787	
G	10.70		11.10	0.421		0.437	
Ν	16.50		17.20	0.649		0.677	
Р	25.00		26.00	0.984	201	1.023	
R	4.00		4.09	0.157	2100	0.161	
U	38.50		39.30	1.515		1.547	
V	30.00		30.30	1.187		1.193	

TO-3 MECHANICAL DATA





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